

Schottky Diode

V_{RRM} = 45 V
 I_{DAV} = 45 A
 V_F = 0.54 V

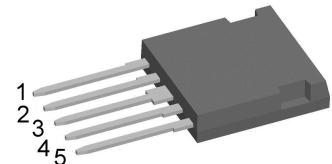
High Performance Schottky Diode

Low Loss and Soft Recovery

3~ Rectifier Bridge

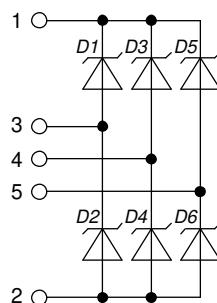
Part number

FUS45-0045B



Backside: isolated

 E72873



Features / Advantages:

- Very low V_F
- Extremely low switching losses
- Low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: i4-Pac

- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

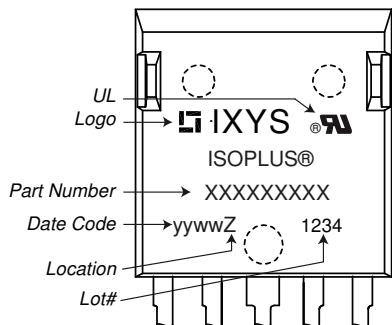
Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

Schottky

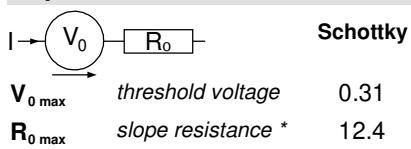
Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$				V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			45	V
I_R	reverse current, drain current	$V_R = 45 V$ $V_R = 45 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		5 50	mA
V_F	forward voltage drop	$I_F = 15 A$ $I_F = 45 A$ $I_F = 15 A$ $I_F = 45 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		0.58 0.82 0.54 0.78	V
I_{DAV}	bridge output current	$T_C = 90^\circ C$ rectangular $d = 0.5$	$T_{VJ} = 150^\circ C$		45	A
V_{F0} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ C$		0.31 14.9	V mΩ
R_{thJC}	thermal resistance junction to case				3.1	K/W
R_{thCH}	thermal resistance case to heatsink			0.2		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		40	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}; V_R = 0 V$	$T_{VJ} = 45^\circ C$		150	A
C_J	junction capacitance	$V_R = 5 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	497		pF

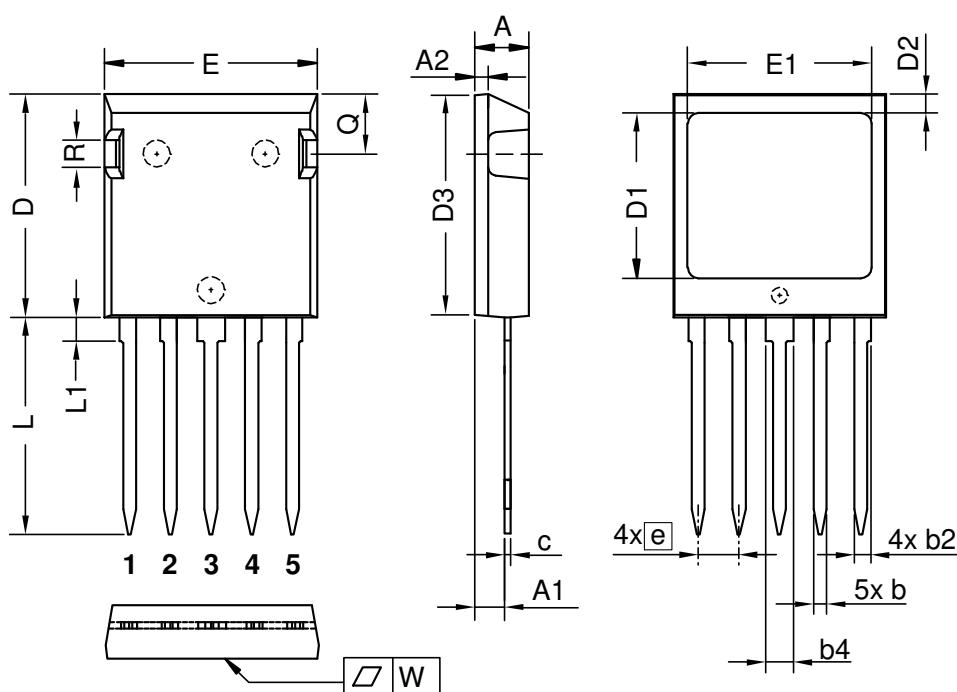
Package i4-Pac

Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			50	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
F_c	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	1.7			mm
$d_{Spb/Apb}$		terminal to backside	5.1			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000 2500			V

Product Marking


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	FUS45-0045B	FUS45-0045B	Tube	25	497762

Equivalent Circuits for Simulation
* on die level
 $T_{VJ} = 150^\circ\text{C}$


Outlines i4-Pac


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.59	3.00	0.102	0.118
A2	1.17	2.16	0.046	0.085
b	1.14	1.40	0.045	0.055
b2	1.47	1.73	0.058	0.068
b4	2.54	2.79	0.100	0.110
c	0.51	0.74	0.020	0.029
D	20.80	21.34	0.819	0.840
D1	14.99	15.75	0.590	0.620
D2	1.65	2.03	0.065	0.080
D3	20.30	20.70	0.799	0.815
E	19.56	20.29	0.770	0.799
E1	16.76	17.53	0.660	0.690
e	3.81	BSC	0.150	BSC
L	19.81	21.34	0.780	0.840
L1	2.11	2.59	0.083	0.102
Q	5.33	6.20	0.210	0.244
R	2.54	4.57	0.100	0.180
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.05 mm über der Kunststoffoberfläche der Bauteilunterseite
The convexbow of substrate is typ. < 0.05 mm over plastic surface level of device bottom side

